

Nanopower BiMOS Op Amp

Features:

- 300-nW (typ.) standby power at $V^+ = 5\text{ V}$
- Supply current, BW, slew rate programmable using external resistor
- 10-pA (typ.) input current
- 5 to 15-V supply
- Output drives typical bipolar-type loads
- Low-cost 8-lead Mini-DIP, TO-5

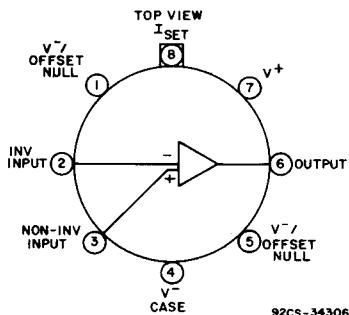
The RCA-CA3440A and CA3440* are integrated circuit operational amplifiers that combine the advantages of MOS and bipolar transistors on a single monolithic chip.

The CA3440A and CA3440 BiMOS op amps feature gate-protected PMOS transistors in the input circuit to provide very-high-input impedance and very-low-input current (10 pA). These devices operate at total supply voltages from 5 to 15 volts and can be operated over the temperature range from -55°C to $+125^\circ\text{C}$. Their virtues are programmability and very low standby power consumption (300 nW). These operational amplifiers are internally phase-compensated to achieve stable operation in the unity-gain follower configuration. Terminals are also provided for use in applications requiring input offset-voltage nulling. The use of PMOS in the input stage results in common-mode input voltage capability down to 0.5 volt below the negative-supply terminals, an important attribute for single-supply applications. The output stage uses MOS complementary source-follower form which permits moderate load driving capability ($10\text{ K}\Omega$) at very low total standby currents (50 nA).

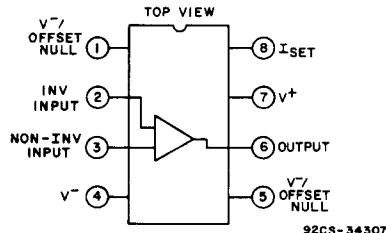
The CA3440A and CA3440 have the same 8-lead terminal pin-out used for "741" and other industry-standard op amps with two exceptions: terminals one and five must be connected to the negative supply or to a potentiometer if nulling is required. Terminal 8 must be programmed through an external resistor returned to the negative supply.

These devices are supplied in either the standard 8-lead TO-5 style package (T suffix), 8-lead dual-in-line formed-lead TO-5 style "DIL-CAN" package (S suffix), or in the 8-lead dual-in-line plastic package "Mini-DIP" (E suffix). They are also available in chip form (H suffix).

* Formerly Dev. Type No. TA10590.



S and T Suffixes



E Suffix

Functional diagrams for CA3440A and CA3440.

CA3440A, CA3440**MAXIMUM RATINGS, Absolute-Maximum Values:****DC SUPPLY VOLTAGE**(BETWEEN V⁺ AND V⁻ TERMINALS) 25 V

DIFFERENTIAL-MODE INPUT VOLTAGE ±9 V

COMMON-MODE DC INPUT VOLTAGE (V⁺ + 8 V) to (V⁻ - 0.5 V)

INPUT-TERMINAL CURRENT 1 mA

DEVICE DISSIPATION:**WITHOUT HEAT SINK —**

UP TO 55°C 630 mW

ABOVE 55°C Derate linearly 6.67 mW/°C

WITH HEAT SINK —

AT 125°C 418 mW

BELOW 125°C Derate linearly 16.7 mW/°C

TEMPERATURE RANGE:**OPERATING** -55 to +125°C**STORAGE** -65 to +150°C**OUTPUT SHORT-CIRCUIT DURATION** INDEFINITE**LEAD TEMPERATURE (DURING SOLDERING):**

AT DISTANCE 1/16 ± 1/32 IN. (1.59 ± 0.79 MM) FROM CASE FOR 10 SECONDS MAX. +265°C

TYPICAL VALUES INTENDED ONLY FOR DESIGN GUIDANCE

CHARACTERISTIC	TEST CONDITIONS		CA3440A	CA3440	UNITS
	V ⁺ =+5 V; V ⁻ =-5 V	R _{SET} =10 MΩ; TA=25°C			
Input Resistance, R _I			2	2	ΤΩ
Input Capacitance, C _T			3.5	3.5	pF
Output Resistance, R _O			450	450	Ω
Equivalent Input	f = 1 kHz	R _S =100 Ω	110	110	nV/√Hz
Noise Voltage, e _n	f=10 kHz		110	110	
Short-Circuit Current					
Source IOM ⁺			15	15	mA
To Opposite Supply					
Sink IOM ⁻			4.5	4.5	
Gain-Bandwidth Product, f _T			63	63	kHz
Slew Rate, SR			0.03	0.03	V/μs
Transient Response					
Rise Time, t _r		R _L = 10 kΩ	5.6	5.6	μs
Overshoot		C _L =100 pF	10	10	%

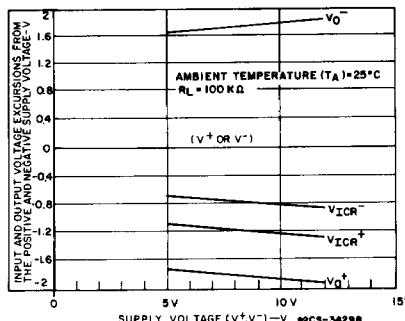


Fig. 1 – Output-voltage-swing and common-mode input-voltage range versus supply voltage.

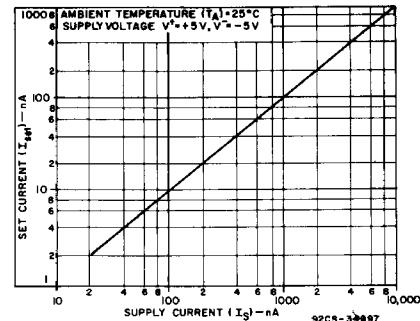


Fig. 2 – Set current versus supply current.

CA3440A, CA3440**ELECTRICAL CHARACTERISTICS FOR EQUIPMENT DESIGN**At $V^+ = +5$ V, $V^- = -5$ V, $T_A = 25^\circ\text{C}$ Unless Otherwise Specified, $R_{SET} = 10 \text{ M}\Omega$

CHARACTERISTIC	LIMITS						UNITS	
	CA3440A			CA3440				
	Min.	Typ.	Max.	Min.	Typ.	Max.		
Input Offset Voltage, $ V_{IO} $	—	2	5	—	5	10	mV	
Input Offset Current, $ I_{IO} $	—	2.5	20	—	2.5	30	pA	
Input Current, $ I_I $	—	10	40	—	10	50		
Large-Signal Voltage Gain, AOL ($R_L = 10 \text{ k}\Omega$)	10K	100K	—	10K	100K	—	V/V	
	80	100	—	80	100	—	dB	
Common-Mode Rejection Ratio, CMRR	—	100	320	—	100	320	$\mu\text{V/V}$	
Common-Mode Input V _{ICR+}	+3.5	+3.7	—	+3.5	+3.7	—	V	
Voltage Range, V _{ICR-}	-5.0	-5.3	—	-5.0	-5.3	—		
Power Supply Rejection Ratio, $\Delta VIO/\Delta V$	—	32	320	—	32	320	$\mu\text{V/V}$	
PSRR	70	90	—	70	90	—	dB	
Maximum Output Voltage, VOM ⁺	+3	+3.2	—	+3	+3.2	—	V	
VOM ⁻	-3	-3.2	—	-3	-3.2	—		
Supply Current, I ⁺	—	10	17	—	10	17	μA	
Device Dissipation, P _D	—	100	170	—	100	170	μW	
Input Offset Voltage Temperature Drift, $\Delta VIO/\Delta T$	—	4	—	—	4	—	$\mu\text{V}/^\circ\text{C}$	

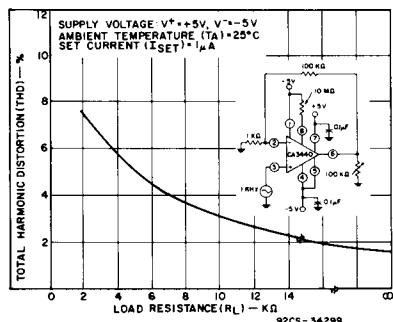


Fig. 3 – Total harmonic distortion percentage versus load resistance.

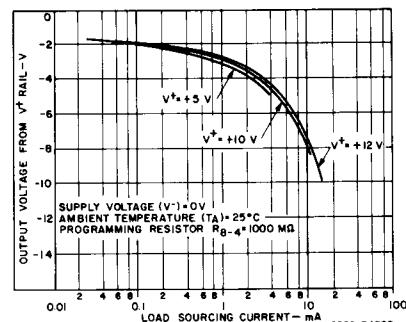


Fig. 4 – Output voltage versus sourcing load current.

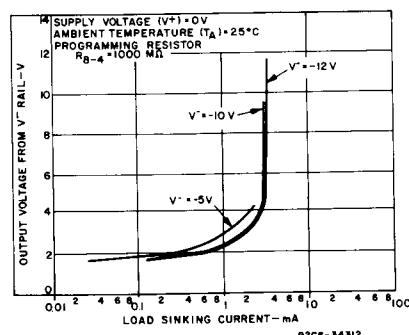


Fig. 5 – Output voltage versus sinking load current.

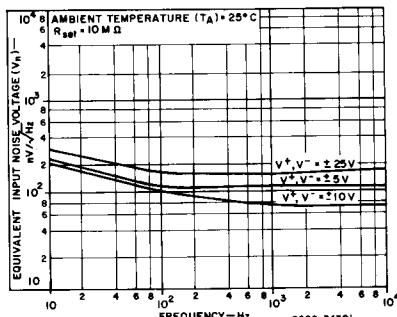


Fig. 6 – Input noise voltage versus frequency.

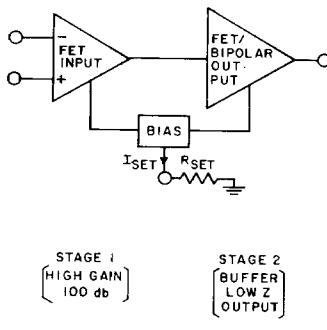
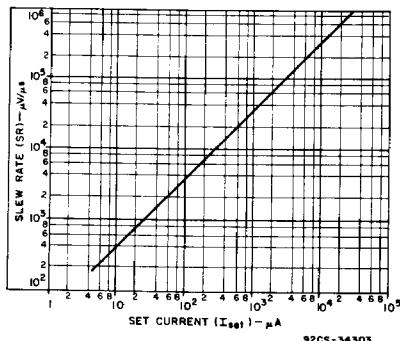
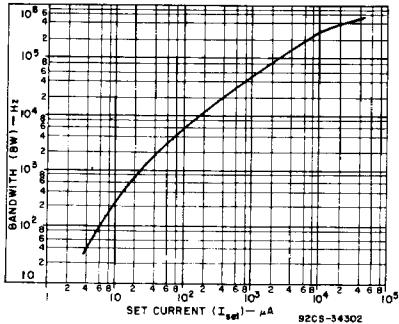
CA3440A, CA3440

Fig. 9 - Nanopower op amp (supply current programmable using R_{SET}) 1-pA typical input bias current, 4.0 to 15-volt supply.

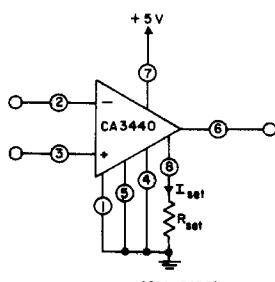


Fig. 10 - Nanopower op amp (usable standby power versus programming resistor R_{SET}).

As R_{SET} is increased, I_{SET} and the standby power decrease while the BW/SR also decreases.

Operating at a +5 V single supply, the CA3440 exhibits the following characteristics:

R_{SET}	Standby Power	BW	SR
1 MΩ	250 nW	164 kHz	0.17 V/μs
10 MΩ	25 μW	27 kHz	0.017 V/μs
100 MΩ	2.5 μW	2.6 kHz	.0017 V/μs
1000 MΩ	250 nW	78 Hz	0.00017 V/μs

The CA3440 is pin-compatible with the 741 except that pins 1 and 5 (typical negative nulling pins) must be connected either directly to pin 4 or to a negative nulling potentiometer. In addition, pin 8, the I_{SET} terminal, must be returned to either ground or $-V$ via R_{SET} .

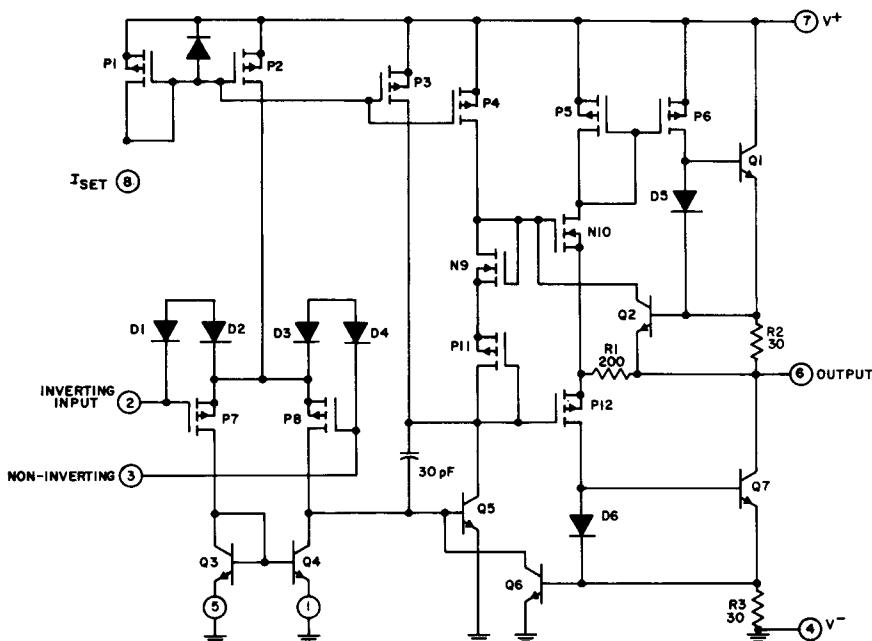
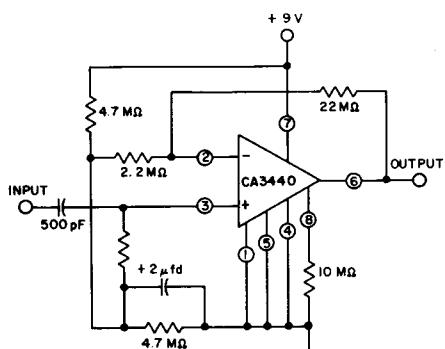
CA3440A, CA3440

Fig. 11 - Schematic diagram for CA3440.

92CM-34308

APPLICATIONS CIRCUITS

$R_{in} > 20 \text{ M}\Omega$
 STAND-BY POWER = $90 \mu\text{W}$
 GAIN = 20 dB
 BW: 20-Hz TO 3-KHz
 SR = $0.016 \text{ V}/\mu\text{s}$

92CS-34309

Fig. 12 - High-input impedance amplifier.

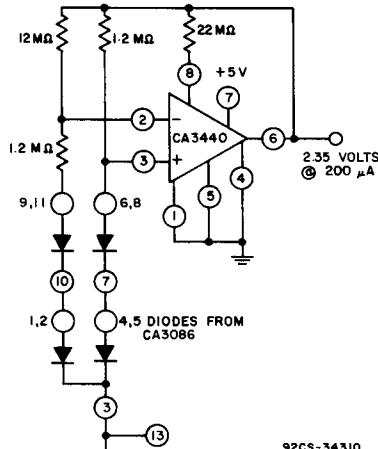
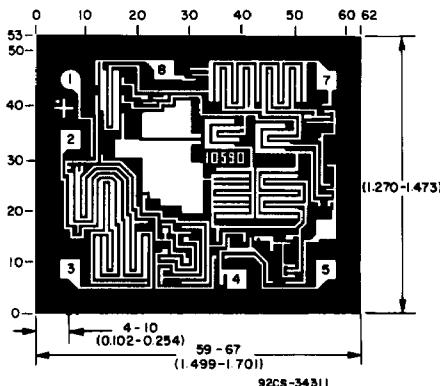


Fig. 13 - Micropower bandgap reference.

CA3440A, CA3440

Dimensions and pad layout for CA3440H.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The layout represents a chip when it is part of the wafer. When the wafer is cut into chips, the cleavage angles are 57° instead of 90° with respect to the face of the chip. Therefore, the isolated chip is actually 7 mils (0.17 mm) larger in both dimensions.